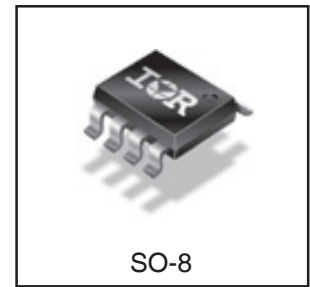
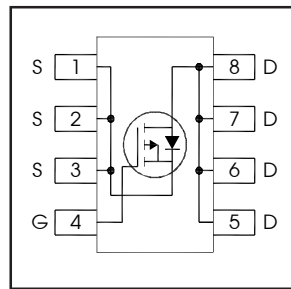


IRF9393PbF

HEXFET® Power MOSFET

| | | |
|---|-------------|-----------|
| V_{DS} | -30 | V |
| $V_{GS\ max}$ | ±25 | V |
| $R_{DS(on)\ max}$ (@ $V_{GS} = -10V$) | 19.4 | mΩ |
| I_D (@ $T_A = 25^\circ C$) | -9.2 | A |



Applications

- Adaptor Input Switch for Notebook PC

Features and Benefits

Features

| |
|--|
| 25V $V_{GS\ max}$ |
| Industry-Standard SO8 Package |
| RoHS Compliant Containing no Lead, no Bromide and no Halogen |

Resulting Benefits

| |
|-------------------------------|
| Direct Drive at High V_{GS} |
| Multi-Vendor Compatibility |
| Environmentally Friendlier |

| Orderable part number | Package Type | Standard Pack | | Note |
|-----------------------|--------------|---------------|----------|------|
| | | Form | Quantity | |
| IRF9393PbF | SO8 | Tube/Bulk | 95 | |
| IRF9393TRPbF | SO8 | Tape and Reel | 4000 | |

Absolute Maximum Ratings

| | Parameter | Max. | Units |
|--------------------------|---|--------------|-------|
| V_{DS} | Drain-to-Source Voltage | -30 | V |
| V_{GS} | Gate-to-Source Voltage | ± 25 | |
| $I_D @ T_A = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | -9.2 | A |
| $I_D @ T_A = 70^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | -7.3 | |
| I_{DM} | Pulsed Drain Current ① | -75 | |
| $P_D @ T_A = 25^\circ C$ | Power Dissipation ④ | 2.5 | W |
| $P_D @ T_A = 70^\circ C$ | Power Dissipation ④ | 1.6 | |
| | Linear Derating Factor | 0.02 | W/°C |
| T_J T_{STG} | Operating Junction and Storage Temperature Range | -55 to + 150 | °C |


Static @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-------------------------------------|--------------------------------------|------|-------|------|-------|---|
| B _V DSS | Drain-to-Source Breakdown Voltage | -30 | — | — | V | V _{GS} = 0V, I _D = -250μA |
| ΔB _V DSS/ΔT _J | Breakdown Voltage Temp. Coefficient | — | 0.019 | — | V/°C | Reference to 25°C, I _D = -1mA |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | 13.3 | — | mΩ | V _{GS} = -20V, I _D = -9.2A ③ |
| | | — | 15.6 | 19.4 | | V _{GS} = -10V, I _D = -9.2A ③ |
| | | — | 25.6 | 32.5 | | V _{GS} = -4.5V, I _D = -7.5A ③ |
| V _{GS(th)} | Gate Threshold Voltage | -1.3 | -1.8 | -2.4 | V | V _{DS} = V _{GS} , I _D = -25μA |
| ΔV _{GS(th)} | Gate Threshold Voltage Coefficient | — | -5.7 | — | mV/°C | |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | -1.0 | μA | V _{DS} = -24V, V _{GS} = 0V |
| | | — | — | -150 | | V _{DS} = -24V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | -10 | μA | V _{GS} = -25V |
| | Gate-to-Source Reverse Leakage | — | — | 10 | | V _{GS} = 25V |
| g _{fs} | Forward Transconductance | 13 | — | — | S | V _{DS} = -10V, I _D = -7.5A |
| Q _g | Total Gate Charge ⑥ | — | 14 | — | nC | V _{DS} = -15V, V _{GS} = -4.5V, I _D = -7.5A |
| Q _g | Total Gate Charge ⑥ | — | 25 | 38 | nC | V _{GS} = -10V |
| Q _{gs} | Gate-to-Source Charge ⑥ | — | 3.5 | — | | V _{DS} = -15V |
| Q _{gd} | Gate-to-Drain Charge ⑥ | — | 6.4 | — | | I _D = -7.5A |
| R _G | Gate Resistance ⑥ | — | 15 | — | Ω | |
| t _{d(on)} | Turn-On Delay Time | — | 16 | — | ns | V _{DD} = -15V, V _{GS} = -4.5V ③ |
| t _r | Rise Time | — | 44 | — | | I _D = -1.0A |
| t _{d(off)} | Turn-Off Delay Time | — | 55 | — | | R _G = 6.8Ω |
| t _f | Fall Time | — | 49 | — | | See Figs. 20a & 20b |
| C _{iss} | Input Capacitance | — | 1110 | — | pF | V _{GS} = 0V |
| C _{oss} | Output Capacitance | — | 230 | — | | V _{DS} = -25V |
| C _{riss} | Reverse Transfer Capacitance | — | 160 | — | | f = 1.0MHz |

Avalanche Characteristics

| | Parameter | Typ. | Max. | Units |
|-----------------|---------------------------------|------|------|-------|
| E _{AS} | Single Pulse Avalanche Energy ② | — | 100 | mJ |
| I _{AR} | Avalanche Current ① | — | -7.5 | A |

Diode Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|-----------------|---|------|------|------|-------|--|
| I _S | Continuous Source Current (Body Diode) | — | — | -2.5 | A | MOSFET symbol showing the integral reverse p-n junction diode.  |
| I _{SM} | Pulsed Source Current (Body Diode) ① | — | — | -75 | | |
| V _{SD} | Diode Forward Voltage | — | — | -1.2 | V | T _J = 25°C, I _S = -2.5A, V _{GS} = 0V ③ |
| t _{rr} | Reverse Recovery Time | — | 24 | 36 | ns | T _J = 25°C, I _F = -2.5A, V _{DD} = -24V |
| Q _{rr} | Reverse Recovery Charge | — | 15 | 23 | nC | di/dt = 100A/μs ③ |

Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|------------------|--------------------------|------|------|-------|
| R _{θJL} | Junction-to-Drain Lead ⑤ | — | 20 | °C/W |
| R _{θJA} | Junction-to-Ambient ④ | — | 50 | |

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting T_J = 25°C, L = 3.5mH, R_G = 25Ω, I_{AS} = -7.5A.
- ③ Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ④ When mounted on 1 inch square copper board.
- ⑤ R_θ is measured at T_J of approximately 90°C.
- ⑥ For DESIGN AID ONLY, not subject to production testing.

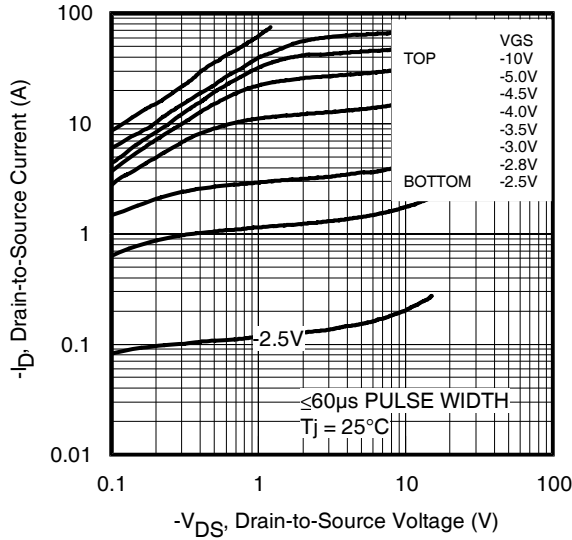


Fig 1. Typical Output Characteristics

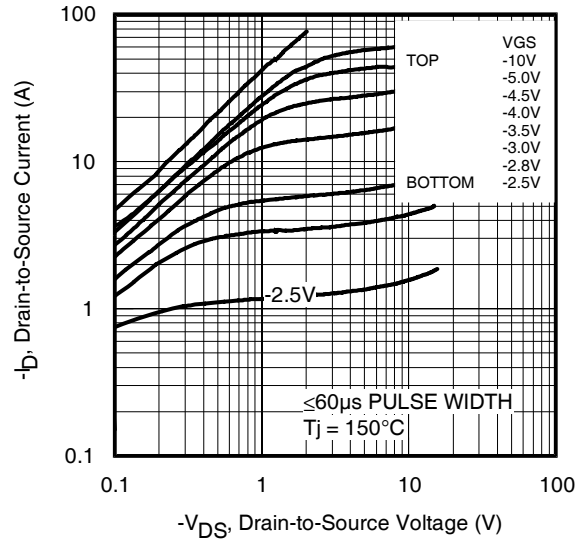


Fig 2. Typical Output Characteristics

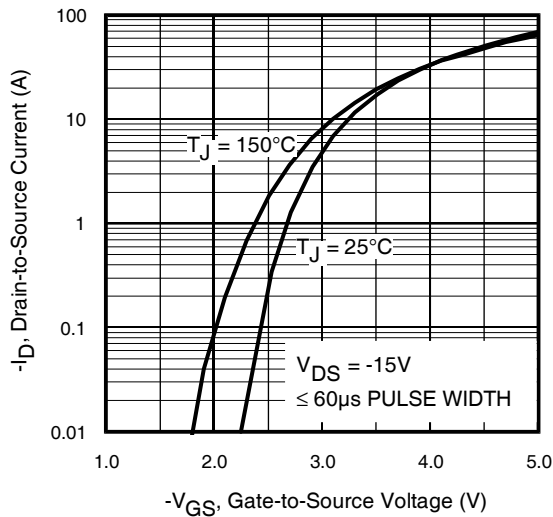


Fig 3. Typical Transfer Characteristics

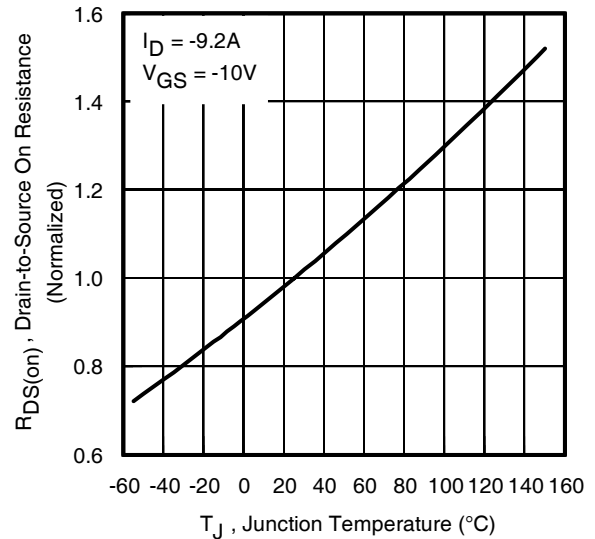


Fig 4. Normalized On-Resistance vs. Temperature

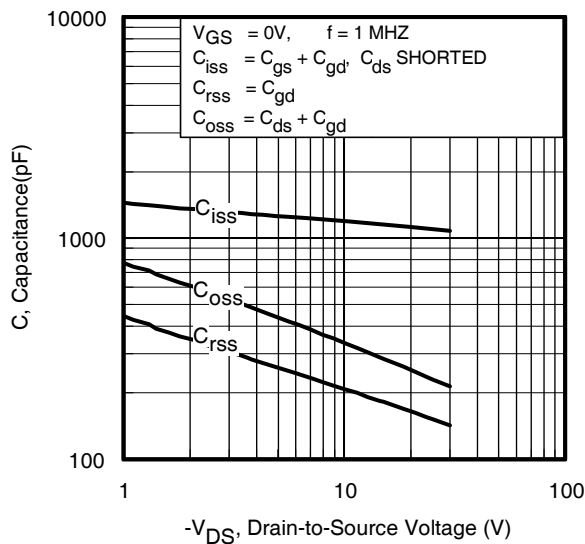


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage
www.irf.com

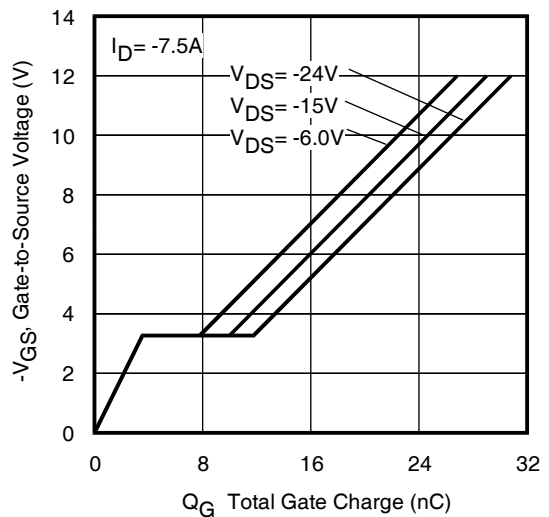


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

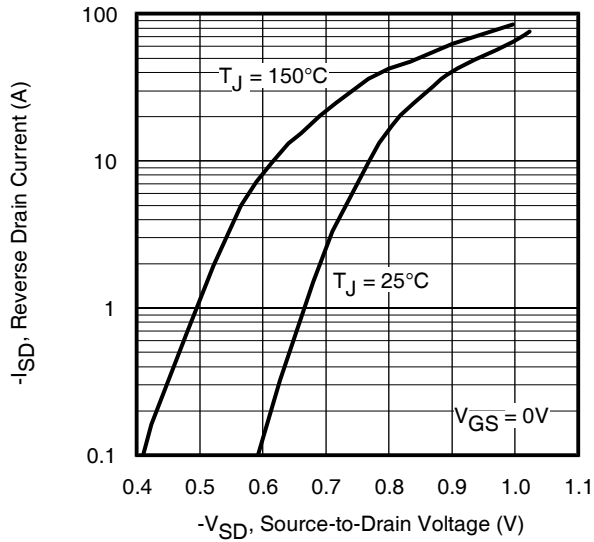


Fig 7. Typical Source-Drain Diode Forward Voltage

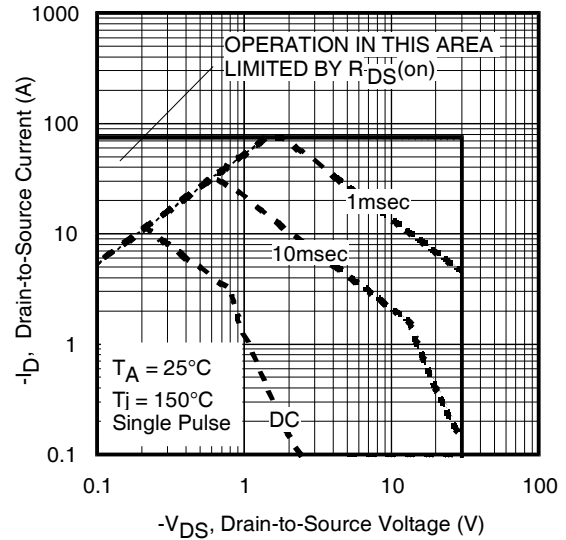


Fig 8. Maximum Safe Operating Area

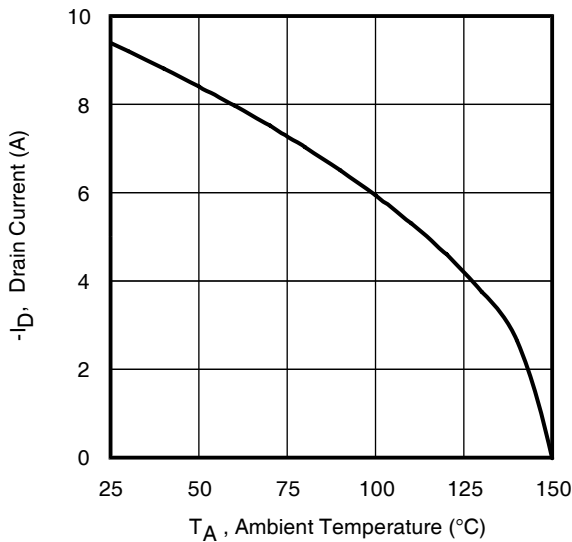


Fig 9. Maximum Drain Current vs. Ambient Temperature

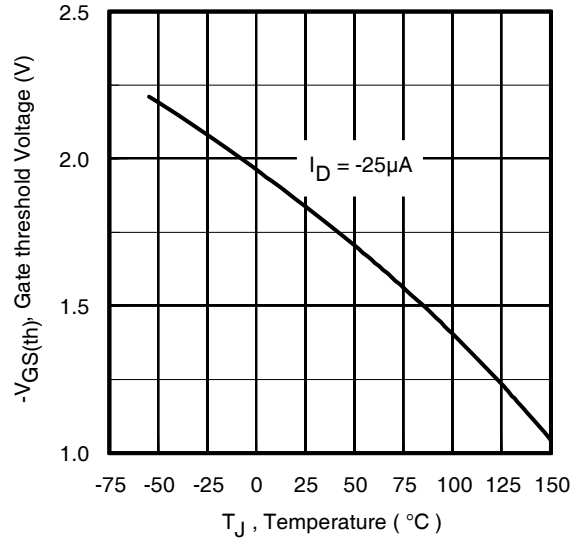


Fig 10. Threshold Voltage vs. Temperature

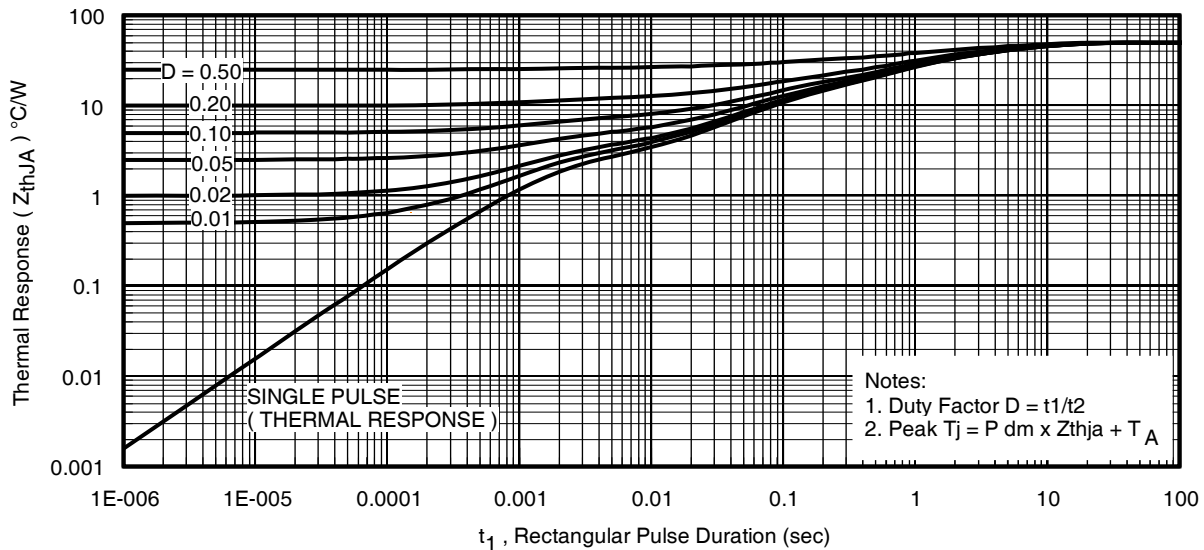


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

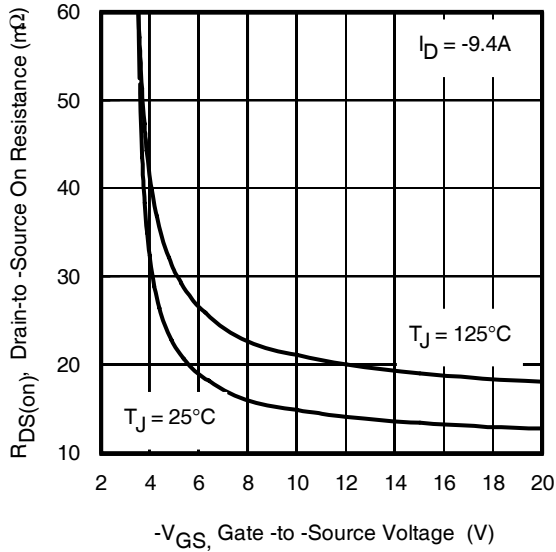


Fig 12. On-Resistance vs. Gate Voltage

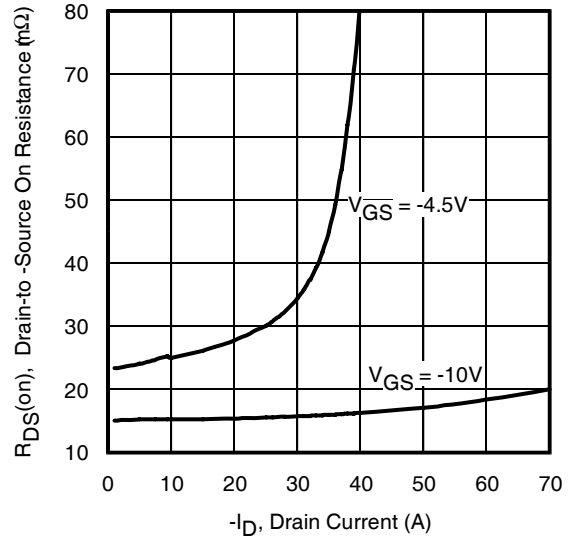


Fig 13. Typical On-Resistance vs. Drain Current

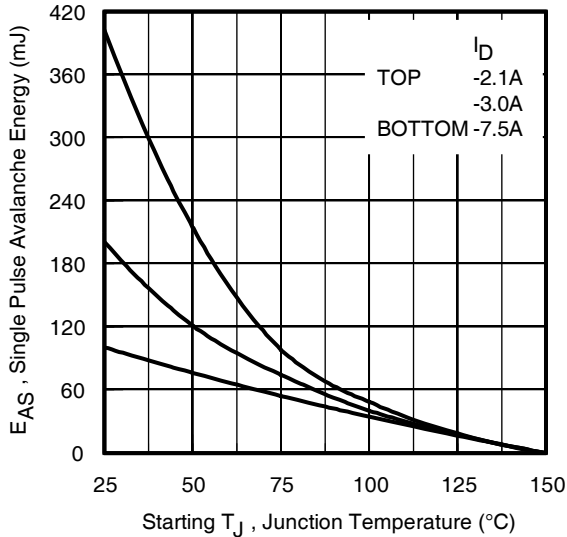


Fig 14. Maximum Avalanche Energy vs. Drain Current

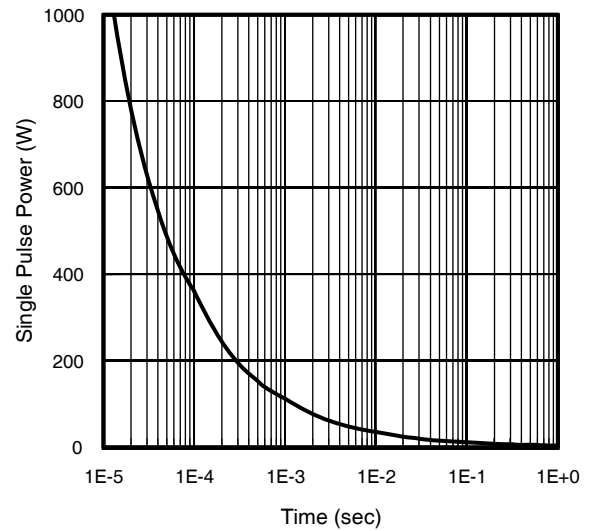
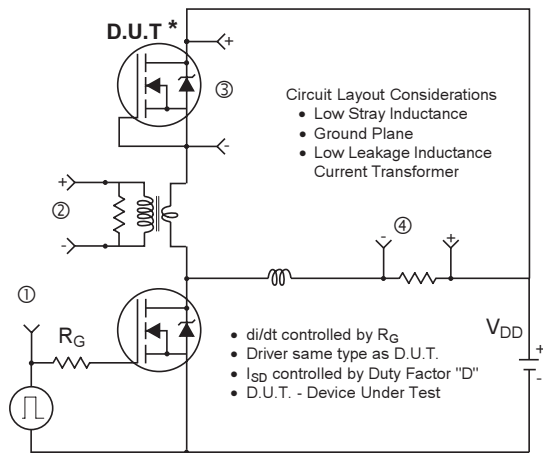
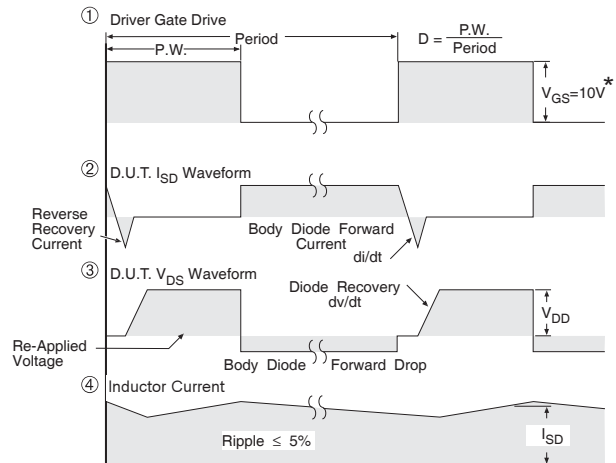


Fig 16. Typical Power vs. Time



* Reverse Polarity of D.U.T. for P-Channel



* $V_{GS} = 5V$ for Logic Level Devices

Fig 17. Diode Reverse Recovery Test Circuit for P-Channel HEXFET® Power MOSFETs

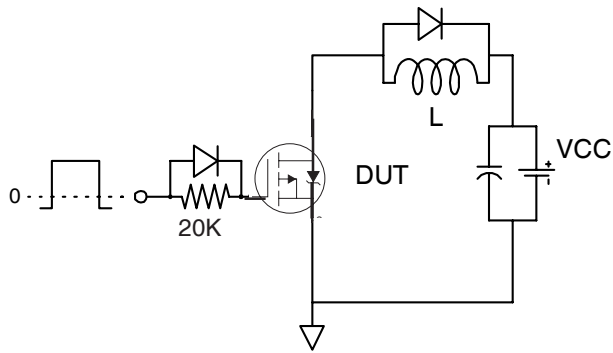


Fig 18a. Gate Charge Test Circuit

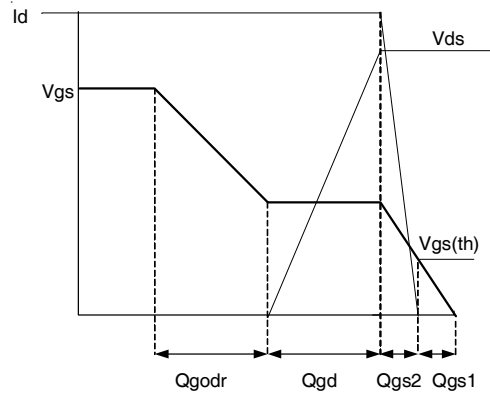


Fig 18b. Gate Charge Waveform

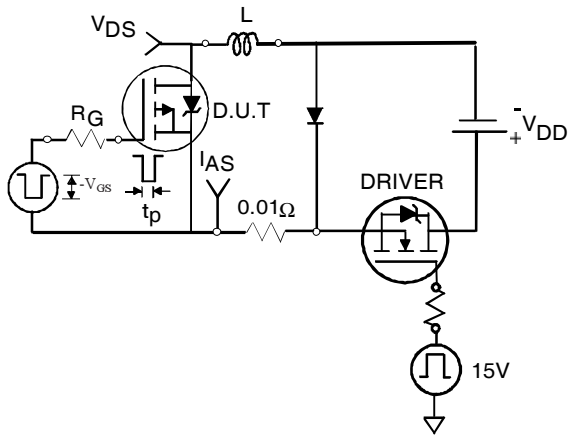


Fig 19a. Unclamped Inductive Test Circuit

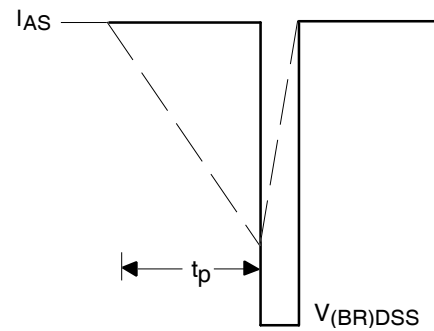


Fig 19b. Unclamped Inductive Waveforms

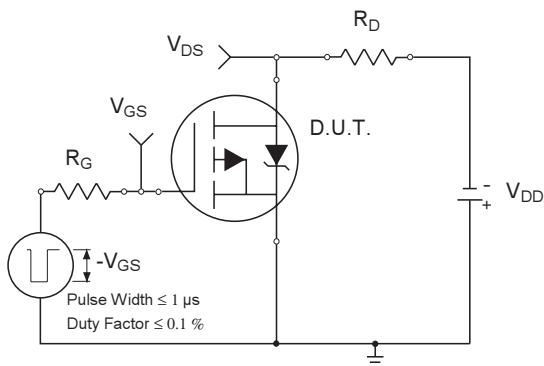


Fig 20a. Switching Time Test Circuit

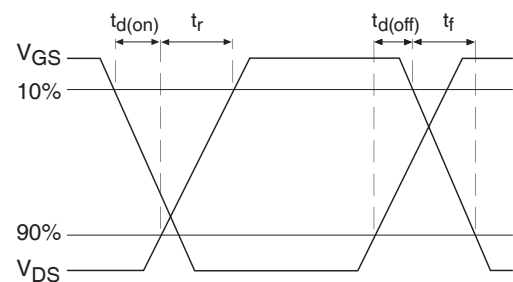
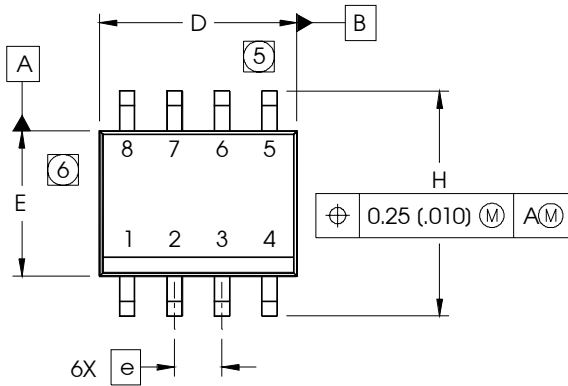


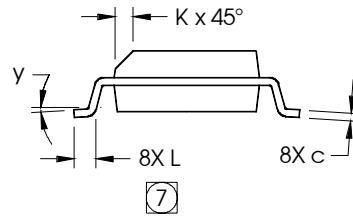
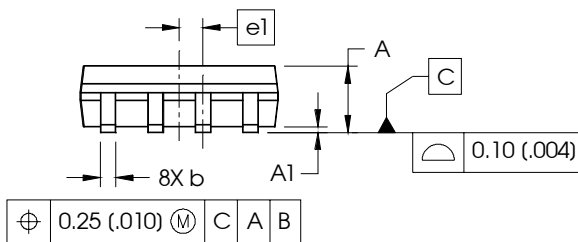
Fig 20b. Switching Time Waveforms

SO-8 Package Outline (MOSFET & Fetky)

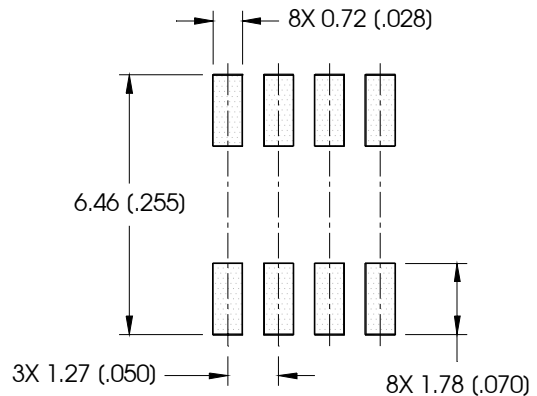
Dimensions are shown in millimeters (inches)



| DIM | INCHES | | MILLIMETERS | |
|-----|------------|-------|-------------|------|
| | MIN | MAX | MIN | MAX |
| A | .0532 | .0688 | 1.35 | 1.75 |
| A1 | .0040 | .0098 | 0.10 | 0.25 |
| b | .013 | .020 | 0.33 | 0.51 |
| c | .0075 | .0098 | 0.19 | 0.25 |
| D | .189 | .1968 | 4.80 | 5.00 |
| E | .1497 | .1574 | 3.80 | 4.00 |
| e | .050 BASIC | | 1.27 BASIC | |
| e1 | .025 BASIC | | 0.635 BASIC | |
| H | .2284 | .2440 | 5.80 | 6.20 |
| K | .0099 | .0196 | 0.25 | 0.50 |
| L | .016 | .050 | 0.40 | 1.27 |
| y | 0° | 8° | 0° | 8° |



FOOTPRINT

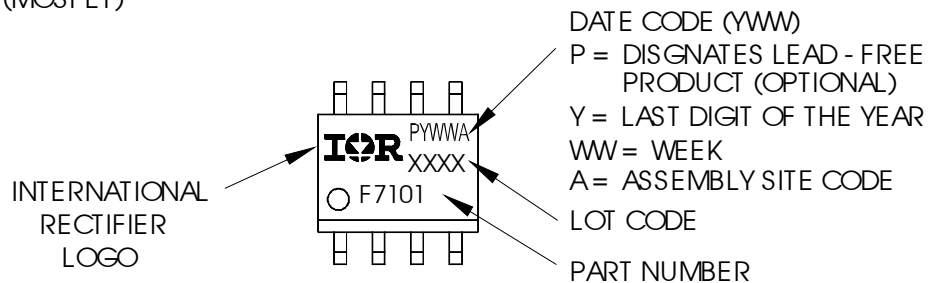


NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

SO-8 Part Marking Information

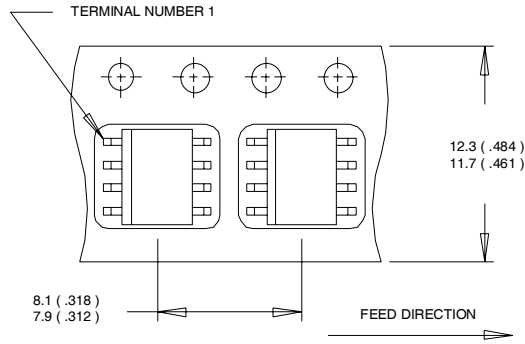
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



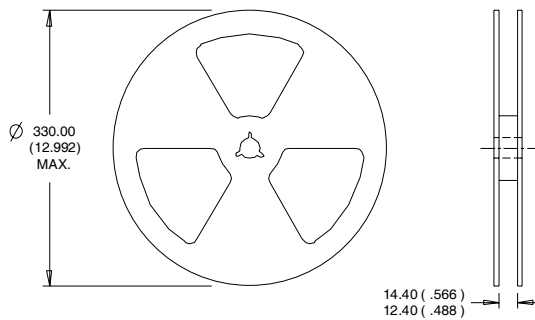
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

IRF9393PbF

SO-8 Tape and Reel (Dimensions are shown in millimeters (inches))



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Qualification Information†

| | | |
|----------------------------|-----------------------------------|-----------------------------------|
| Qualification level | Consumer †† | |
| | (per JEDEC JESD47F††† guidelines) | |
| Moisture Sensitivity Level | SO-8 | MSL1 (per JEDEC J-STD-020D†††) |
| RoHS Compliant | Yes | |

† Qualification standards can be found at International Rectifier's web site
<http://www.irf.com/product-info/reliability>

†† Higher qualification ratings may be available should the user have such requirements.
Please contact your International Rectifier sales representative for further information:
<http://www.irf.com/whoto-call/salesrep/>

††† Applicable version of JEDEC standard at the time of product release.

Data and specifications subject to change without notice.